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Figure 1(A) to 1(C) are diagrams that overview the processes involved in the manufacture of a semiconductor in a first embodiment of the present invention and show a cross-section through the structure;

IN THE CLAIMS:

Please amend the claims as follows:

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1. A semiconductor device, comprising:
 - an underlayer;
 - a base oxide film with holes and formed on the underlayer;
 - a plurality of nitride film patterns with a hole pattern formed on the base oxide film and directly above said holes;
 - an upper oxide film provided on top of said base oxide film to cover the nitride film patterns, the upper oxide film having formed therethrough an plurality of wiring grooves which each exposes part of an associated nitride film pattern including said hole patterns; and
 - wiring metal that fills part of the exposed nitride film patterns, said holes, and said wiring grooves;
 - and wherein said nitride film patterns are formed with such a shape and size that surrounds the outside of their associated wiring groove and are separate from neighbouring nitride film patterns.

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3. A semiconductor device, comprising:
- an underlayer;
 - a base oxide film with holes formed on the underlayer;
 - a plurality of nitride film patterns with a hole pattern provided on the base oxide film and formed directly above said holes;
 - an upper oxide film provided on top of said base oxide film to cover the nitride film patterns, the upper oxide film having formed therethrough a plurality of wiring grooves which each exposes part of an associated nitride film pattern including said hole patterns; and
 - wiring metal that fills part of the exposed nitride film pattern, said holes, and said wiring grooves;
 - and wherein outer shape of said nitride film pattern is substantially the same as the shape of the opening of said wiring groove, an internal wall surface of said wiring groove is tapered from the opening on the upper surface of said upper oxide film to upper surface of said nitride film pattern and neighbouring nitride film patterns are separate from each other.
4. A semiconductor device, comprising:
- an underlayer;
 - a base oxide film formed on the underlayer, the base oxide film having formed therethrough a plurality of holes;

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an upper oxide film provided on the base oxide film, the upper oxide film having formed therethrough wiring grooves which are connected to said holes; and

wiring metal that fills said holes and said wiring grooves, said wiring metal having a first portion around the periphery of said hole having a first diameter and a second portion at a middle section of said upper oxide film above said first portion having a diameter smaller than the first diameter.
